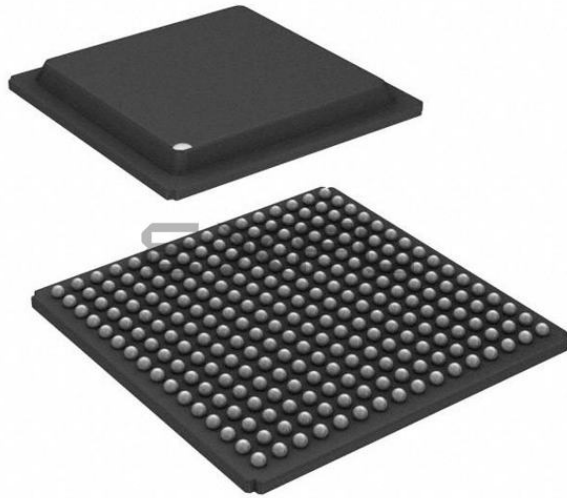




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

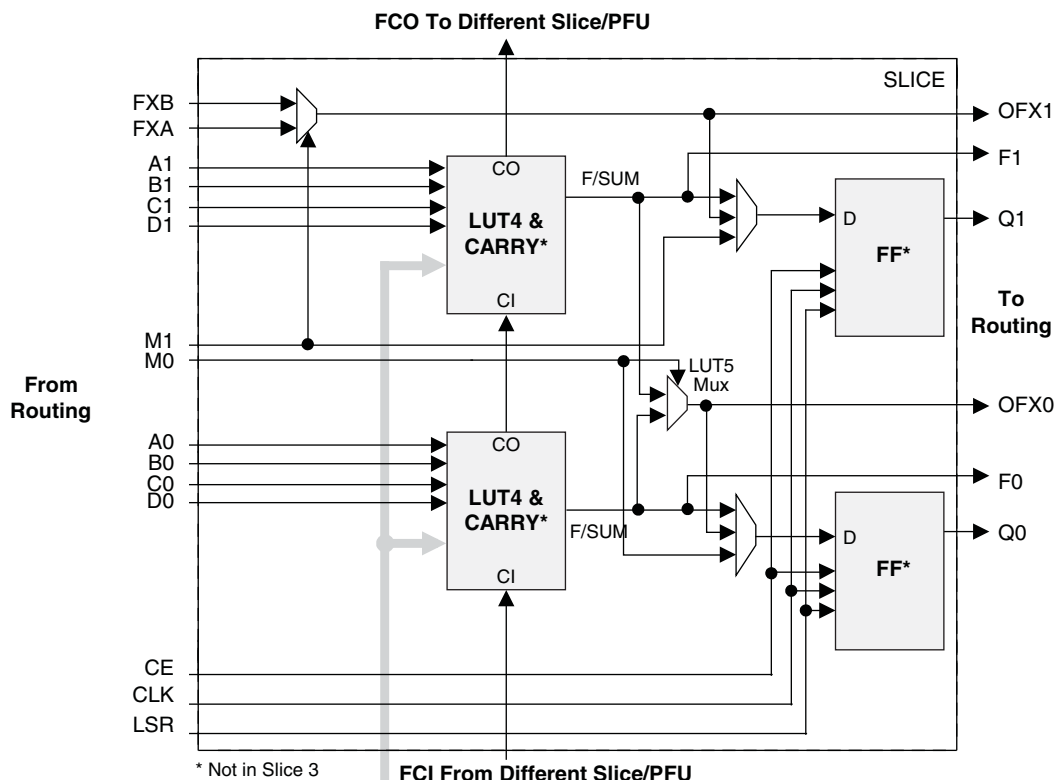
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	2125
Number of Logic Elements/Cells	17000
Total RAM Bits	716800
Number of I/O	133
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-BGA
Supplier Device Package	256-FTBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-17ea-8ftn256i

Figure 2-3. Slice Diagram



For Slices 0 and 1, memory control signals are generated from Slice 2 as follows:

WCK is CLK

WRE is from LSR

DI[3:2] for Slice 1 and DI[1:0] for Slice 0 data from Slice 2

WAD [A:D] is a 4-bit address from slice 2 LUT input

Table 2-2. Slice Signal Descriptions

Function	Type	Signal Names	Description
Input	Data signal	A0, B0, C0, D0	Inputs to LUT4
Input	Data signal	A1, B1, C1, D1	Inputs to LUT4
Input	Multi-purpose	M0	Multipurpose Input
Input	Multi-purpose	M1	Multipurpose Input
Input	Control signal	CE	Clock Enable
Input	Control signal	LSR	Local Set/Reset
Input	Control signal	CLK	System Clock
Input	Inter-PFU signal	FC	Fast Carry-in ¹
Input	Inter-slice signal	FXA	Intermediate signal to generate LUT6 and LUT7
Input	Inter-slice signal	FXB	Intermediate signal to generate LUT6 and LUT7
Output	Data signals	F0, F1	LUT4 output register bypass signals
Output	Data signals	Q0, Q1	Register outputs
Output	Data signals	OFX0	Output of a LUT5 MUX
Output	Data signals	OFX1	Output of a LUT6, LUT7, LUT8 ² MUX depending on the slice
Output	Inter-PFU signal	FCO	Slice 2 of each PFU is the fast carry chain output ¹

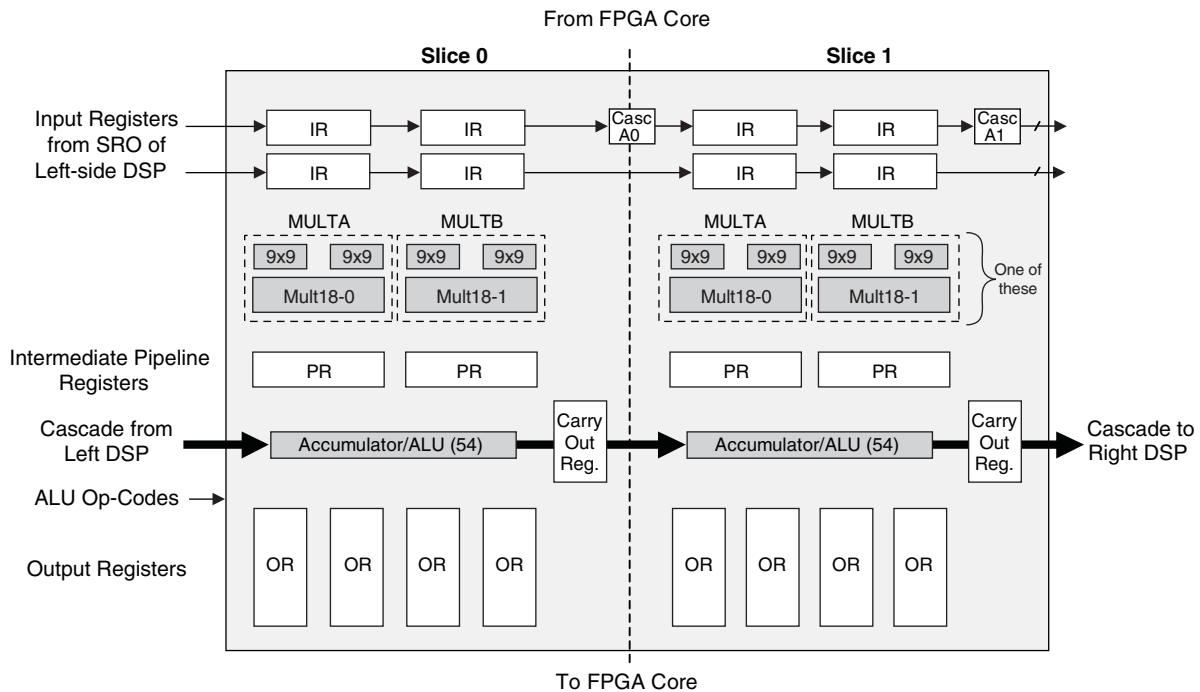
1. See Figure 2-3 for connection details.

2. Requires two PFUs.

- as, overflow, underflow and convergent rounding, etc.
- Flexible cascading across slices to get larger functions
- RTL Synthesis friendly synchronous reset on all registers, while still supporting asynchronous reset for legacy users
- Dynamic MUX selection to allow Time Division Multiplexing (TDM) of resources for applications that require processor-like flexibility that enables different functions for each clock cycle

For most cases, as shown in Figure 2-24, the LatticeECP3 DSP slice is backwards-compatible with the LatticeECP2™ sysDSP block, such that, legacy applications can be targeted to the LatticeECP3 sysDSP slice. The functionality of one LatticeECP2 sysDSP Block can be mapped into two adjacent LatticeECP3 sysDSP slices, as shown in Figure 2-25.

Figure 2-24. Simplified sysDSP Slice Block Diagram



DLL Calibrated DQS Delay Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces, a PLL is used for this adjustment. However, in DDR memories the clock (referred to as DQS) is not free-running so this approach cannot be used. The DQS Delay block provides the required clock alignment for DDR memory interfaces.

The delay required for the DQS signal is generated by two dedicated DLLs (DDR DLL) on opposite side of the device. Each DLL creates DQS delays in its half of the device as shown in Figure 2-36. The DDR DLL on the left side will generate delays for all the DQS Strobe pins on Banks 0, 7 and 6 and DDR DLL on the right will generate delays for all the DQS pins on Banks 1, 2 and 3. The DDR DLL loop compensates for temperature, voltage and process variations by using the system clock and DLL feedback loop. DDR DLL communicates the required delay to the DQS delay block using a 7-bit calibration bus (DCNTL[6:0])

The DQS signal (selected PIOs only, as shown in Figure 2-35) feeds from the PAD through a DQS control logic block to a dedicated DQS routing resource. The DQS control logic block consists of DQS Read Control logic block that generates control signals for the read side and DQS Write Control logic that generates the control signals required for the write side. A more detailed DQS control diagram is shown in Figure 2-37, which shows how the DQS control blocks interact with the data paths.

The DQS Read control logic receives the delay generated by the DDR DLL on its side and delays the incoming DQS signal by 90 degrees. This delayed ECLKDQSR is routed to 10 or 11 DQ pads covered by that DQS signal. This block also contains a polarity control logic that generates a DDRCLKPOL signal, which controls the polarity of the clock to the sync registers in the input register blocks. The DQS Read control logic also generates a DDRLAT signal that is in the input register block to transfer data from the first set of DDR register to the second set of DDR registers when using the DDRX2 gearbox mode for DDR3 memory interface.

The DQS Write control logic block generates the DQCLK0 and DQCLK1 clocks used to control the output gearing in the Output register block which generates the DDR data output and the DQS output. They are also used to control the generation of the DQS output through the DQS output register block. In addition to the DCNTL [6:0] input from the DDR DLL, the DQS Write control block also uses a Dynamic Delay DYN DEL [7:0] attribute which is used to further delay the DQS to accomplish the write leveling found in DDR3 memory. Write leveling is controlled by the DDR memory controller implementation. The DYN DELAY can set 128 possible delay step settings. In addition, the most significant bit will invert the clock for a 180-degree shift of the incoming clock. This will generate the DQSW signal used to generate the DQS output in the DQS output register block.

Figure 2-36 and Figure 2-37 show how the DQS transition signals that are routed to the PIOs.

Please see TN1180, [LatticeECP3 High-Speed I/O Interface](#) for more information on this topic.

Figure 2-40. SERDES/PCS Quads (LatticeECP3-150)

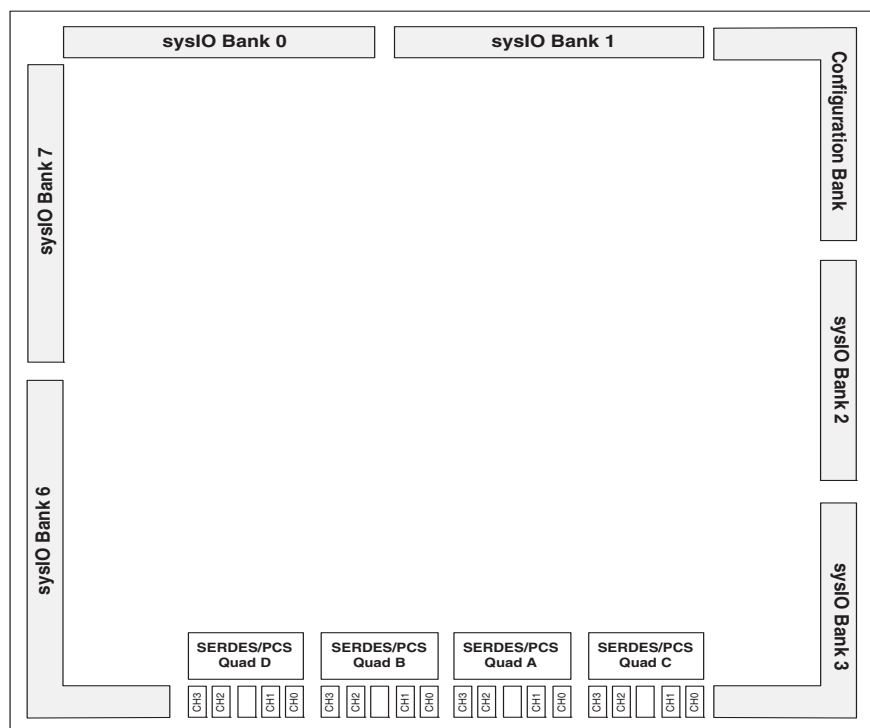


Table 2-13. LatticeECP3 SERDES Standard Support

Standard	Data Rate (Mbps)	Number of General/Link Width	Encoding Style
PCI Express 1.1	2500	x1, x2, x4	8b10b
Gigabit Ethernet	1250, 2500	x1	8b10b
SGMII	1250	x1	8b10b
XAUI	3125	x4	8b10b
Serial RapidIO Type I, Serial RapidIO Type II, Serial RapidIO Type III	1250, 2500, 3125	x1, x4	8b10b
CPRI-1, CPRI-2, CPRI-3, CPRI-4	614.4, 1228.8, 2457.6, 3072.0	x1	8b10b
SD-SDI (259M, 344M)	143 ¹ , 177 ¹ , 270, 360, 540	x1	NRZI/Scrambled
HD-SDI (292M)	1483.5, 1485	x1	NRZI/Scrambled
3G-SDI (424M)	2967, 2970	x1	NRZI/Scrambled
SONET-STS-3 ²	155.52	x1	N/A
SONET-STS-12 ²	622.08	x1	N/A
SONET-STS-48 ²	2488	x1	N/A

1. For slower rates, the SERDES are bypassed and CML signals are directly connected to the FPGA routing.

2. The SONET protocol is supported in 8-bit SERDES mode. See TN1176 [Lattice ECP3 SERDES/PCS Usage Guide](#) for more information.

BLVDS25

The LatticeECP3 devices support the BLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS25 Multi-point Output Example

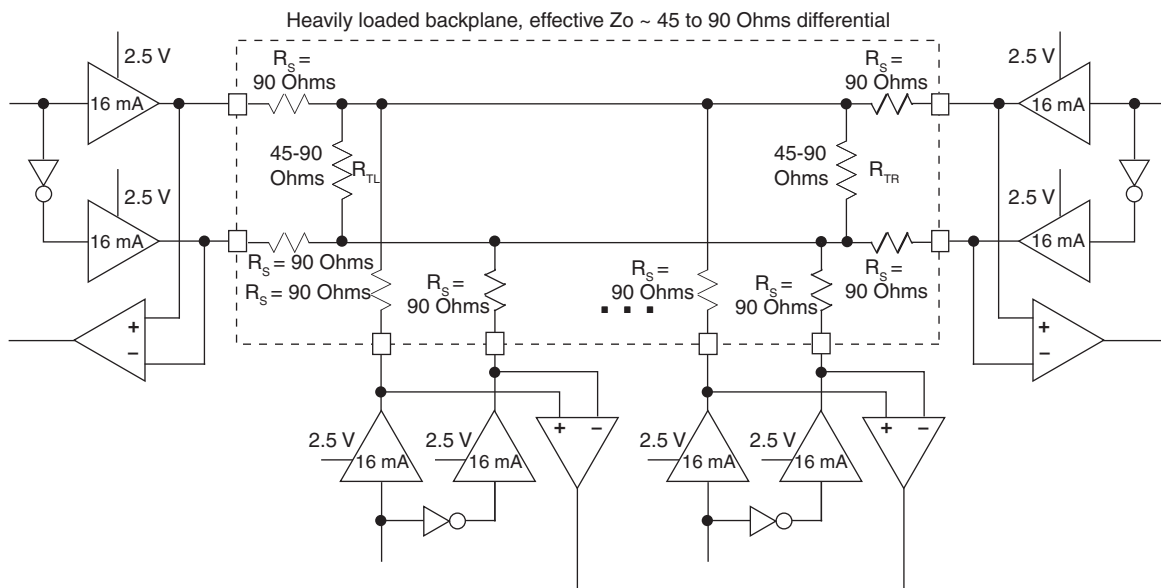


Table 3-2. BLVDS25 DC Conditions¹

Over Recommended Operating Conditions

Parameter	Description	Typical		Units
		Zo = 45Ω	Zo = 90Ω	
V _{CCIO}	Output Driver Supply (+/- 5%)	2.50	2.50	V
Z _{OUT}	Driver Impedance	10.00	10.00	Ω
R _S	Driver Series Resistor (+/- 1%)	90.00	90.00	Ω
R _{TL}	Driver Parallel Resistor (+/- 1%)	45.00	90.00	Ω
R _{TR}	Receiver Termination (+/- 1%)	45.00	90.00	Ω
V _{OH}	Output High Voltage	1.38	1.48	V
V _{OL}	Output Low Voltage	1.12	1.02	V
V _{OD}	Output Differential Voltage	0.25	0.46	V
V _{CM}	Output Common Mode Voltage	1.25	1.25	V
I _{DC}	DC Output Current	11.24	10.20	mA

1. For input buffer, see LVDS table.

LVPECL33

The LatticeECP3 devices support the differential LVPECL standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The LVPECL input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-3 is one possible solution for point-to-point signals.

Figure 3-3. Differential LVPECL33

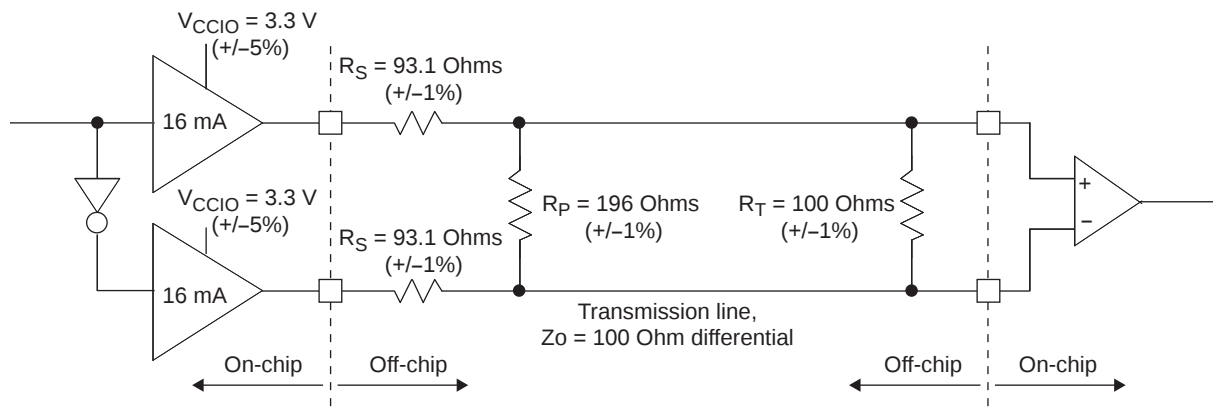


Table 3-3. LVPECL33 DC Conditions¹

Over Recommended Operating Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply (+/-5%)	3.30	V
Z_{OUT}	Driver Impedance	10	Ω
R_S	Driver Series Resistor (+/-1%)	93	Ω
R_P	Driver Parallel Resistor (+/-1%)	196	Ω
R_T	Receiver Termination (+/-1%)	100	Ω
V_{OH}	Output High Voltage	2.05	V
V_{OL}	Output Low Voltage	1.25	V
V_{OD}	Output Differential Voltage	0.80	V
V_{CM}	Output Common Mode Voltage	1.65	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	12.11	mA

1. For input buffer, see LVDS table.

Register-to-Register Performance^{1, 2, 3}

Function	-8 Timing	Units
18x18 Multiply/Accumulate (Input & Output Registers)	200	MHz
18x18 Multiply-Add/Sub (All Registers)	400	MHz

1. These timing numbers were generated using ispLEVER tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
2. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.
3. For details on -9 speed grade devices, please contact your Lattice Sales Representative.

Derating Timing Tables

Logic timing provided in the following sections of this data sheet and the Diamond and ispLEVER design tools are worst case numbers in the operating range. Actual delays at nominal temperature and voltage for best case process, can be much better than the values given in the tables. The Diamond and ispLEVER design tools can provide logic timing numbers at a particular temperature and voltage.

LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	-8		-7		-6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
t _{HPLL}	Clock to Data Hold - PIO Input Register	ECP3-70EA/95EA	0.7	—	0.7	—	0.8	—	ns
t _{SU_DELP}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-70EA/95EA	1.6	—	1.8	—	2.0	—	ns
t _{H_DELP}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	—	ns
t _{COPLL}	Clock to Output - PIO Output Register	ECP3-35EA	—	3.2	—	3.4	—	3.6	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-35EA	0.6	—	0.7	—	0.8	—	ns
t _{HPLL}	Clock to Data Hold - PIO Input Register	ECP3-35EA	0.3	—	0.3	—	0.4	—	ns
t _{SU_DELP}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-35EA	1.6	—	1.7	—	1.8	—	ns
t _{H_DELP}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-35EA	0.0	—	0.0	—	0.0	—	ns
t _{COPLL}	Clock to Output - PIO Output Register	ECP3-17EA	—	3.0	—	3.3	—	3.5	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-17EA	0.6	—	0.7	—	0.8	—	ns
t _{HPLL}	Clock to Data Hold - PIO Input Register	ECP3-17EA	0.3	—	0.3	—	0.4	—	ns
t _{SU_DELP}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-17EA	1.6	—	1.7	—	1.8	—	ns
t _{H_DELP}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
Generic DDR¹²									
Generic DDRX1 Inputs with Clock and Data (>10 Bits Wide) Centered at Pin (GDDR1_RX.SCLK.Centered) Using PCLK Pin for Clock Input									
t _{SUGDDR}	Data Setup Before CLK	All ECP3EA Devices	480	—	480	—	480	—	ps
t _{HOGDDR}	Data Hold After CLK	All ECP3EA Devices	480	—	480	—	480	—	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	All ECP3EA Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Inputs with Clock and Data (>10 Bits Wide) Aligned at Pin (GDDR1_RX.SCLK.PLL.Aligned) Using PLLCLKIN Pin for Clock Input									
Data Left, Right, and Top Sides and Clock Left and Right Sides									
t _{DVACKGDDR}	Data Setup Before CLK	All ECP3EA Devices	—	0.225	—	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	All ECP3EA Devices	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDR1 Clock Frequency	All ECP3EA Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Inputs with Clock and Data (>10 Bits Wide) Aligned at Pin (GDDR1_RX.SCLK.Aligned) Using DLL - CLKIN Pin for Clock Input									
Data Left, Right and Top Sides and Clock Left and Right Sides									
t _{DVACKGDDR}	Data Setup Before CLK	All ECP3EA Devices	—	0.225	—	0.225	—	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	All ECP3EA Devices	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDR1 Clock Frequency	All ECP3EA Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Inputs with Clock and Data (<10 Bits Wide) Centered at Pin (GDDR1_RX.DQS.Centered) Using DQS Pin for Clock Input									
t _{SUGDDR}	Data Setup After CLK	All ECP3EA Devices	535	—	535	—	535	—	ps
t _{HOGDDR}	Data Hold After CLK	All ECP3EA Devices	535	—	535	—	535	—	ps
f _{MAX_GDDR}	DDR1 Clock Frequency	All ECP3EA Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Inputs with Clock and Data (<10bits wide) Aligned at Pin (GDDR1_RX.DQS.Aligned) Using DQS Pin for Clock Input									
Data and Clock Left and Right Sides									
t _{DVACKGDDR}	Data Setup Before CLK	All ECP3EA Devices	—	0.225	—	0.225	—	0.225	UI

LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	-8		-7		-6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
$t_{DVECLKGDDR}$	Data Hold After CLK	All ECP3EA Devices	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDR1 Clock Frequency	All ECP3EA Devices	—	250	—	250	—	250	MHz
Generic DDRX2 Inputs with Clock and Data (>10 Bits Wide) Centered at Pin (GDDR2_RX.ECLK.Centered) Using PCLK Pin for Clock Input									
Left and Right Sides									
t_{SUGDDR}	Data Setup Before CLK	ECP3-150EA	321	—	403	—	471	—	ps
t_{HOGDDR}	Data Hold After CLK	ECP3-150EA	321	—	403	—	471	—	ps
f_{MAX_GDDR}	DDR2 Clock Frequency	ECP3-150EA	—	405	—	325	—	280	MHz
t_{SUGDDR}	Data Setup Before CLK	ECP3-70EA/95EA	321	—	403	—	535	—	ps
t_{HOGDDR}	Data Hold After CLK	ECP3-70EA/95EA	321	—	403	—	535	—	ps
f_{MAX_GDDR}	DDR2 Clock Frequency	ECP3-70EA/95EA	—	405	—	325	—	250	MHz
t_{SUGDDR}	Data Setup Before CLK	ECP3-35EA	335	—	425	—	535	—	ps
t_{HOGDDR}	Data Hold After CLK	ECP3-35EA	335	—	425	—	535	—	ps
f_{MAX_GDDR}	DDR2 Clock Frequency	ECP3-35EA	—	405	—	325	—	250	MHz
t_{SUGDDR}	Data Setup Before CLK	ECP3-17EA	335	—	425	—	535	—	ps
t_{HOGDDR}	Data Hold After CLK	ECP3-17EA	335	—	425	—	535	—	ps
f_{MAX_GDDR}	DDR2 Clock Frequency	ECP3-17EA	—	405	—	325	—	250	MHz
Generic DDRX2 Inputs with Clock and Data (>10 Bits Wide) Aligned at Pin (GDDR2_RX.ECLK.Aligned)									
Left and Right Side Using DLLCLKIN Pin for Clock Input									
$t_{DVACLGDDR}$	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDR2 Clock Frequency	ECP3-150EA	—	460	—	385	—	345	MHz
$t_{DVACLGDDR}$	Data Setup Before CLK	ECP3-70EA/95EA	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDR2 Clock Frequency	ECP3-70EA/95EA	—	460	—	385	—	311	MHz
$t_{DVACLGDDR}$	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	—	0.210	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790	—	UI
f_{MAX_GDDR}	DDR2 Clock Frequency	ECP3-35EA	—	460	—	385	—	311	MHz
$t_{DVACLGDDR}$	Data Setup Before CLK	ECP3-17EA	—	0.210	—	0.210	—	0.210	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
f_{MAX_GDDR}	DDR2 Clock Frequency	ECP3-17EA	—	460	—	385	—	311	MHz
Top Side Using PCLK Pin for Clock Input									
$t_{DVACLGDDR}$	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDR2 Clock Frequency	ECP3-150EA	—	235	—	170	—	130	MHz
$t_{DVACLGDDR}$	Data Setup Before CLK	ECP3-70EA/95EA	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDR2 Clock Frequency	ECP3-70EA/95EA	—	235	—	170	—	130	MHz
$t_{DVACLGDDR}$	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	—	0.210	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790	—	UI
f_{MAX_GDDR}	DDR2 Clock Frequency	ECP3-35EA	—	235	—	170	—	130	MHz
$t_{DVACLGDDR}$	Data Setup Before CLK	ECP3-17EA	—	0.210	—	0.210	—	0.210	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
f_{MAX_GDDR}	DDR2 Clock Frequency	ECP3-17EA	—	235	—	170	—	130	MHz

LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	-8		-7		-6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDRX2 Inputs with Clock and Data (>10bits wide) are Aligned at Pin (GDDR2_RX.ECLK.Aligned) (No CLKDIV)									
Left and Right Sides Using DLLCLKPIN for Clock Input									
tDVACKGDDR	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
tDVECLKGDDR	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	—	UI
fMAX_GDDR	DDR2 Clock Frequency	ECP3-150EA	—	460	—	385	—	345	MHz
tDVACKGDDR	Data Setup Before CLK	ECP3-70EA/95EA	—	0.225	—	0.225	—	0.225	UI
tDVECLKGDDR	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	—	UI
fMAX_GDDR	DDR2 Clock Frequency	ECP3-70EA/95EA	—	460	—	385	—	311	MHz
tDVACKGDDR	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	—	0.210	UI
tDVECLKGDDR	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790	—	UI
fMAX_GDDR	DDR2 Clock Frequency	ECP3-35EA	—	460	—	385	—	311	MHz
tDVACKGDDR	Data Setup Before CLK (Left and Right Sides)	ECP3-17EA	—	0.210	—	0.210	—	0.210	UI
tDVECLKGDDR	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
fMAX_GDDR	DDR2 Clock Frequency	ECP3-17EA	—	460	—	385	—	311	MHz
Top Side Using PCLK Pin for Clock Input									
tDVACKGDDR	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
tDVECLKGDDR	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	—	UI
fMAX_GDDR	DDR2 Clock Frequency	ECP3-150EA	—	235	—	170	—	130	MHz
tDVACKGDDR	Data Setup Before CLK	ECP3-70EA/95EA	—	0.225	—	0.225	—	0.225	UI
tDVECLKGDDR	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	—	UI
fMAX_GDDR	DDR2 Clock Frequency	ECP3-70EA/95EA	—	235	—	170	—	130	MHz
tDVACKGDDR	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	—	0.210	UI
tDVECLKGDDR	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790	—	UI
fMAX_GDDR	DDR2 Clock Frequency	ECP3-35EA	—	235	—	170	—	130	MHz
tDVACKGDDR	Data Setup Before CLK	ECP3-17EA	—	0.210	—	0.210	—	0.210	UI
tDVECLKGDDR	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
fMAX_GDDR	DDR2 Clock Frequency	ECP3-17EA	—	235	—	170	—	130	MHz
Generic DDRX2 Inputs with Clock and Data (<10 Bits Wide) Centered at Pin (GDDR2_RX.DQS.Centered) Using DQS Pin for Clock Input									
Left and Right Sides									
tSUGDDR	Data Setup Before CLK	All ECP3EA Devices	330	—	330	—	352	—	ps
tHOGDDR	Data Hold After CLK	All ECP3EA Devices	330	—	330	—	352	—	ps
fMAX_GDDR	DDR2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz
Generic DDRX2 Inputs with Clock and Data (<10 Bits Wide) Aligned at Pin (GDDR2_RX.DQS.Aligned) Using DQS Pin for Clock Input									
Left and Right Sides									
tDVACKGDDR	Data Setup Before CLK	All ECP3EA Devices	—	0.225	—	0.225	—	0.225	UI
tDVECLKGDDR	Data Hold After CLK	All ECP3EA Devices	0.775	—	0.775	—	0.775	—	UI
fMAX_GDDR	DDR2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz
Generic DDRX1 Output with Clock and Data (>10 Bits Wide) Centered at Pin (GDDR1_TX.SCLK.Centered) ¹⁰									
tDVBGDDR	Data Valid Before CLK	ECP3-150EA	670	—	670	—	670	—	ps
tDVAGDDR	Data Valid After CLK	ECP3-150EA	670	—	670	—	670	—	ps
fMAX_GDDR	DDR1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
tDVBGDDR	Data Valid Before CLK	ECP3-70EA/95EA	666	—	665	—	664	—	ps
tDVAGDDR	Data Valid After CLK	ECP3-70EA/95EA	666	—	665	—	664	—	ps

The figure contains two timing diagrams. The top diagram, titled "Transmit Parameters", shows the relationship between the clock (CLK) and the data bus (Data (TDAT, TCTL)). It illustrates the setup and hold times for the transmit data path. The setup time is labeled $t_{DIBGDDR}$ and the hold time is labeled $t_{DIAGDDR}$. The data bus is shown with multiple data bursts, each preceded by a setup period and followed by a hold period. The bottom diagram, titled "Receive Parameters", shows the relationship between the receive clock (RDTCLK) and the data bus (Data (RDAT, RCTL)). It illustrates the setup and hold times for the receive data path. The setup time is labeled $t_{DVACKGDDR}$ and the hold time is labeled $t_{DVECKGDDR}$. The data bus is shown with multiple data bursts, each preceded by a setup period and followed by a hold period.

The figure contains two timing diagrams, one for Transmit Parameters and one for Receive Parameters, showing the relationship between DQS and DQ signals.

Transmit Parameters: This diagram shows the DQS signal (purple) and the DQ signal (green). The DQ signal is divided into four segments, each marked with a cross-hatch pattern. The timing parameters are defined as follows:

- t_{DQVBS} : The time interval from the rising edge of DQS to the start of the first DQ data burst.
- t_{DQVAS} : The time interval from the falling edge of DQS to the end of the last DQ data burst.

Receive Parameters: This diagram shows the DQS signal (purple) and the DQ signal (green). The DQ signal is divided into four segments, each marked with a cross-hatch pattern. The timing parameters are defined as follows:

- t_{DVADQ} : The time interval from the rising edge of DQS to the start of the first DQ data burst.
- t_{DVEDQ} : The time interval from the falling edge of DQS to the end of the last DQ data burst.

LatticeECP3 Family Timing Adders^{1, 2, 3, 4, 5, 7} (Continued)
Over Recommended Commercial Operating Conditions

Buffer Type	Description	–8	–7	–6	Units
RS2S25	RS2S, VCCIO = 2.5 V	–0.07	–0.04	–0.01	ns
PPLVDS	Point-to-Point LVDS, True LVDS, VCCIO = 2.5 V or 3.3 V	–0.22	–0.19	–0.16	ns
LVPECL33	LVPECL, Emulated, VCCIO = 3.3 V	0.67	0.76	0.86	ns
HSTL18_I	HSTL_18 class I 8mA drive, VCCIO = 1.8 V	1.20	1.34	1.47	ns
HSTL18_II	HSTL_18 class II, VCCIO = 1.8 V	0.89	1.00	1.11	ns
HSTL18D_I	Differential HSTL 18 class I 8 mA drive	1.20	1.34	1.47	ns
HSTL18D_II	Differential HSTL 18 class II	0.89	1.00	1.11	ns
HSTL15_I	HSTL_15 class I 4 mA drive, VCCIO = 1.5 V	1.67	1.83	1.99	ns
HSTL15D_I	Differential HSTL 15 class I 4 mA drive	1.67	1.83	1.99	ns
SSTL33_I	SSTL_3 class I, VCCIO = 3.3 V	1.12	1.17	1.21	ns
SSTL33_II	SSTL_3 class II, VCCIO = 3.3 V	1.08	1.12	1.15	ns
SSTL33D_I	Differential SSTL_3 class I	1.12	1.17	1.21	ns
SSTL33D_II	Differential SSTL_3 class II	1.08	1.12	1.15	ns
SSTL25_I	SSTL_2 class I 8 mA drive, VCCIO = 2.5 V	1.06	1.19	1.31	ns
SSTL25_II	SSTL_2 class II 16 mA drive, VCCIO = 2.5 V	1.04	1.17	1.31	ns
SSTL25D_I	Differential SSTL_2 class I 8 mA drive	1.06	1.19	1.31	ns
SSTL25D_II	Differential SSTL_2 class II 16 mA drive	1.04	1.17	1.31	ns
SSTL18_I	SSTL_1.8 class I, VCCIO = 1.8 V	0.70	0.84	0.97	ns
SSTL18_II	SSTL_1.8 class II 8 mA drive, VCCIO = 1.8 V	0.70	0.84	0.97	ns
SSTL18D_I	Differential SSTL_1.8 class I	0.70	0.84	0.97	ns
SSTL18D_II	Differential SSTL_1.8 class II 8 mA drive	0.70	0.84	0.97	ns
SSTL15	SSTL_1.5, VCCIO = 1.5 V	1.22	1.35	1.48	ns
SSTL15D	Differential SSTL_15	1.22	1.35	1.48	ns
LVTTTL33_4mA	LVTTTL 4 mA drive, VCCIO = 3.3V	0.25	0.24	0.23	ns
LVTTTL33_8mA	LVTTTL 8 mA drive, VCCIO = 3.3V	–0.06	–0.06	–0.07	ns
LVTTTL33_12mA	LVTTTL 12 mA drive, VCCIO = 3.3V	–0.01	–0.02	–0.02	ns
LVTTTL33_16mA	LVTTTL 16 mA drive, VCCIO = 3.3V	–0.07	–0.07	–0.08	ns
LVTTTL33_20mA	LVTTTL 20 mA drive, VCCIO = 3.3V	–0.12	–0.13	–0.14	ns
LVC MOS33_4mA	LVC MOS 3.3 4 mA drive, fast slew rate	0.25	0.24	0.23	ns
LVC MOS33_8mA	LVC MOS 3.3 8 mA drive, fast slew rate	–0.06	–0.06	–0.07	ns
LVC MOS33_12mA	LVC MOS 3.3 12 mA drive, fast slew rate	–0.01	–0.02	–0.02	ns
LVC MOS33_16mA	LVC MOS 3.3 16 mA drive, fast slew rate	–0.07	–0.07	–0.08	ns
LVC MOS33_20mA	LVC MOS 3.3 20 mA drive, fast slew rate	–0.12	–0.13	–0.14	ns
LVC MOS25_4mA	LVC MOS 2.5 4 mA drive, fast slew rate	0.12	0.10	0.09	ns
LVC MOS25_8mA	LVC MOS 2.5 8 mA drive, fast slew rate	–0.05	–0.06	–0.07	ns
LVC MOS25_12mA	LVC MOS 2.5 12 mA drive, fast slew rate	0.00	0.00	0.00	ns
LVC MOS25_16mA	LVC MOS 2.5 16 mA drive, fast slew rate	–0.12	–0.13	–0.14	ns
LVC MOS25_20mA	LVC MOS 2.5 20 mA drive, fast slew rate	–0.12	–0.13	–0.14	ns
LVC MOS18_4mA	LVC MOS 1.8 4 mA drive, fast slew rate	0.11	0.12	0.14	ns
LVC MOS18_8mA	LVC MOS 1.8 8 mA drive, fast slew rate	0.11	0.12	0.14	ns
LVC MOS18_12mA	LVC MOS 1.8 12 mA drive, fast slew rate	–0.04	–0.03	–0.03	ns
LVC MOS18_16mA	LVC MOS 1.8 16 mA drive, fast slew rate	–0.04	–0.03	–0.03	ns

SERDES High Speed Data Receiver

Table 3-9. Serial Input Data Specifications

Symbol	Description	Min.	Typ.	Max.	Units
RX-CID _S	Stream of nontransitions ¹ (CID = Consecutive Identical Digits) @ 10 ⁻¹² BER	3.125 G	—	136	Bits
		2.5 G	—	144	
		1.485 G	—	160	
		622 M	—	204	
		270 M	—	228	
		150 M	—	296	
V _{RX-DIFF-S}	Differential input sensitivity	150	—	1760	mV, p-p
V _{RX-IN}	Input levels	0	—	V _{CCA} +0.5 ⁴	V
V _{RX-CM-DC}	Input common mode range (DC coupled)	0.6	—	V _{CCA}	V
V _{RX-CM-AC}	Input common mode range (AC coupled) ³	0.1	—	V _{CCA} +0.2	V
T _{RX-RELOCK}	SCDR re-lock time ²	—	1000	—	Bits
Z _{RX-TERM}	Input termination 50/75 Ohm/High Z	-20%	50/75/HiZ	+20%	Ohms
RL _{RX-RL}	Return loss (without package)	10	—	—	dB

1. This is the number of bits allowed without a transition on the incoming data stream when using DC coupling.
2. This is the typical number of bit times to re-lock to a new phase or frequency within +/- 300 ppm, assuming 8b10b encoded data.
3. AC coupling is used to interface to LVPECL and LVDS. LVDS interfaces are found in laser drivers and Fibre Channel equipment. LVDS interfaces are generally found in 622 Mbps SERDES devices.
4. Up to 1.76 V.

Input Data Jitter Tolerance

A receiver's ability to tolerate incoming signal jitter is very dependent on jitter type. High speed serial interface standards have recognized the dependency on jitter type and have specifications to indicate tolerance levels for different jitter types as they relate to specific protocols. Sinusoidal jitter is considered to be a worst case jitter type.

Table 3-10. Receiver Total Jitter Tolerance Specification

Description	Frequency	Condition	Min.	Typ.	Max.	Units
Deterministic	3.125 Gbps	600 mV differential eye	—	—	0.47	UI, p-p
Random		600 mV differential eye	—	—	0.18	UI, p-p
Total		600 mV differential eye	—	—	0.65	UI, p-p
Deterministic	2.5 Gbps	600 mV differential eye	—	—	0.47	UI, p-p
Random		600 mV differential eye	—	—	0.18	UI, p-p
Total		600 mV differential eye	—	—	0.65	UI, p-p
Deterministic	1.25 Gbps	600 mV differential eye	—	—	0.47	UI, p-p
Random		600 mV differential eye	—	—	0.18	UI, p-p
Total		600 mV differential eye	—	—	0.65	UI, p-p
Deterministic	622 Mbps	600 mV differential eye	—	—	0.47	UI, p-p
Random		600 mV differential eye	—	—	0.18	UI, p-p
Total		600 mV differential eye	—	—	0.65	UI, p-p

Note: Values are measured with CJPAT, all channels operating, FPGA Logic active, I/Os around SERDES pins quiet, voltages are nominal, room temperature.

Serial Rapid I/O Type 2/CPRI LV E.24 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-15. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}^1	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX_DIFF_DC}$	Differential impedance		80	100	120	Ohms
$J_{TX_DDJ}^{3, 4, 5}$	Output data deterministic jitter		—	—	0.17	UI
$J_{TX_TJ}^{2, 3, 4, 5}$	Total output data jitter		—	—	0.35	UI

1. Rise and Fall times measured with board trace, connector and approximately 2.5pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
5. Values are measured at 2.5 Gbps.

Table 3-16. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 2.5 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 2.5 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
$J_{RX_DJ}^{2, 3, 4, 5}$	Deterministic jitter tolerance (peak-to-peak)		—	—	0.37	UI
$J_{RX_RJ}^{2, 3, 4, 5}$	Random jitter tolerance (peak-to-peak)		—	—	0.18	UI
$J_{RX_SJ}^{2, 3, 4, 5}$	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.10	UI
$J_{RX_TJ}^{1, 2, 3, 4, 5}$	Total jitter tolerance (peak-to-peak)		—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.
2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 2.5 Gbps.

SMPTE SD/HD-SDI/3G-SDI (Serial Digital Interface) Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-19. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
BR _{SDO}	Serial data rate		270	—	2975	Mbps
T _{JALIGNMENT} ²	Serial output jitter, alignment	270 Mbps	—	—	0.20	UI
T _{JALIGNMENT} ²	Serial output jitter, alignment	1485 Mbps	—	—	0.20	UI
T _{JALIGNMENT} ^{1,2}	Serial output jitter, alignment	2970Mbps	—	—	0.30	UI
T _{JTIMING}	Serial output jitter, timing	270 Mbps	—	—	0.20	UI
T _{JTIMING}	Serial output jitter, timing	1485 Mbps	—	—	1.0	UI
T _{JTIMING}	Serial output jitter, timing	2970 Mbps	—	—	2.0	UI

Notes:

- Timing jitter is measured in accordance with SMPTE RP 184-1996, SMPTE RP 192-1996 and the applicable serial data transmission standard, SMPTE 259M-1997 or SMPTE 292M (proposed). A color bar test pattern is used. The value of f_{SCLK} is 270 MHz or 360 MHz for SMPTE 259M, 540 MHz for SMPTE 344M or 1485 MHz for SMPTE 292M serial data rates. See the Timing Jitter Bandpass section.
- Jitter is defined in accordance with SMPTE RP1 184-1996 as: jitter at an equipment output in the absence of input jitter.
- All Tx jitter is measured at the output of an industry standard cable driver; connection to the cable driver is via a 50 Ohm impedance differential signal from the Lattice SERDES device.
- The cable driver drives: RL=75 Ohm, AC-coupled at 270, 1485, or 2970 Mbps, RREFLVL=RREFPRE=4.75 kOhm 1%.

Table 3-20. Receive

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
BR _{SDI}	Serial input data rate		270	—	2970	Mbps
CID	Stream of non-transitions (=Consecutive Identical Digits)		7(3G)/26(SMPTE Triple rates) @ 10-12 BER	—	—	Bits

Table 3-21. Reference Clock

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
F _{VCLK}	Video output clock frequency		27	—	74.25	MHz
DC _V	Duty cycle, video clock		45	50	55	%

HDMI (High-Definition Multimedia Interface) Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-22. Transmit and Receive^{1, 2}

Symbol	Description	Spec. Compliance		Units
		Min. Spec.	Max. Spec.	
Transmit				
Intra-pair Skew		—	75	ps
Inter-pair Skew		—	800	ps
TMDS Differential Clock Jitter		—	0.25	UI
Receive				
R _T	Termination Resistance	40	60	Ohms
V _{ICM}	Input AC Common Mode Voltage (50-Ohm Setting)	—	50	mV
TMDS Clock Jitter	Clock Jitter Tolerance	—	0.25	UI

1. Output buffers must drive a translation device. Max. speed is 2 Gbps. If translation device does not modify rise/fall time, the maximum speed is 1.5 Gbps.
2. Input buffers must be AC coupled in order to support the 3.3 V common mode. Generally, HDMI inputs are terminated by an external cable equalizer before data/clock is forwarded to the LatticeECP3 device.

Figure 3-30. SPI Configuration Waveforms

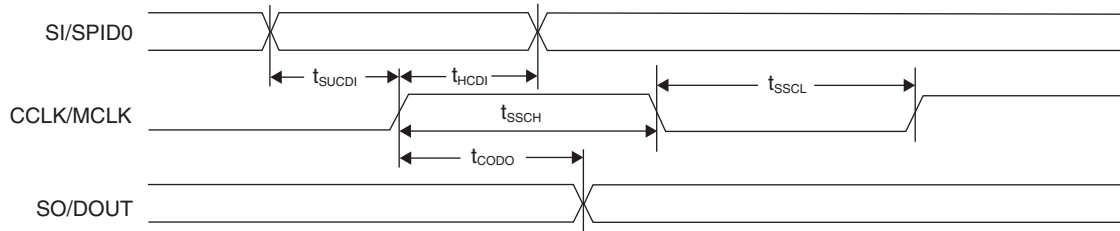
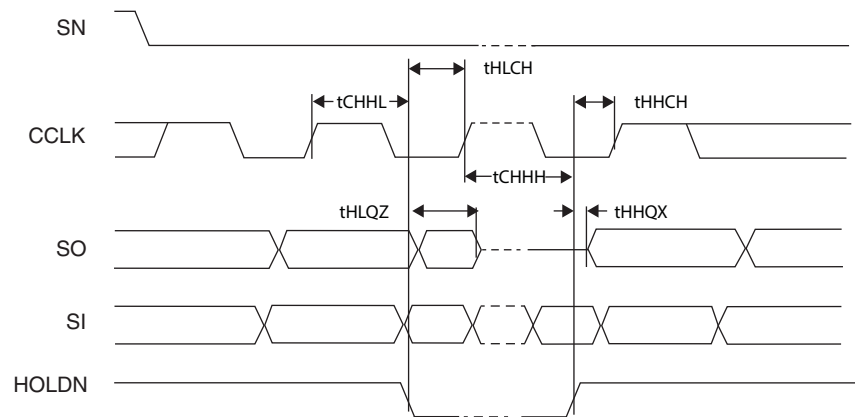


Figure 3-31. Slave SPI HOLDN Waveforms



Part Number	Voltage	Grade ¹	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672I	1.2 V	–6	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7FN672I	1.2 V	–7	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8FN672I	1.2 V	–8	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6LFN672I	1.2 V	–6	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7LFN672I	1.2 V	–7	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8LFN672I	1.2 V	–8	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6FN1156I	1.2 V	–6	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7FN1156I	1.2 V	–7	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8FN1156I	1.2 V	–8	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-6LFN1156I	1.2 V	–6	LOW	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7LFN1156I	1.2 V	–7	LOW	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8LFN1156I	1.2 V	–8	LOW	Lead-Free fpBGA	1156	IND	149

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672ITW ¹	1.2 V	–6	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7FN672ITW ¹	1.2 V	–7	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8FN672ITW ¹	1.2 V	–8	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6FN1156ITW ¹	1.2 V	–6	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7FN1156ITW ¹	1.2 V	–7	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8FN1156ITW ¹	1.2 V	–8	STD	Lead-Free fpBGA	1156	IND	149

1. Specifications for the LFE3-150EA-*sp*FN*pkg*CTW and LFE3-150EA-*sp*FN*pkg*ITW devices, (where *sp* is the speed and *pkg* is the package), are the same as the LFE3-150EA-*sp*FN*pkg*C and LFE3-150EA-*sp*FN*pkg*I devices respectively, except as specified below.

- The CTC (Clock Tolerance Circuit) inside the SERDES hard PCS in the TW device is not functional but it can be bypassed and implemented in soft IP.
- The SERDES XRES pin on the TW device passes CDM testing at 250V.

For Further Information

A variety of technical notes for the LatticeECP3 family are available on the Lattice website at www.latticesemi.com.

- TN1169, [LatticeECP3 sysCONFIG Usage Guide](#)
- TN1176, [LatticeECP3 SERDES/PCS Usage Guide](#)
- TN1177, [LatticeECP3 sysIO Usage Guide](#)
- TN1178, [LatticeECP3 sysCLOCK PLL/DLL Design and Usage Guide](#)
- TN1179, [LatticeECP3 Memory Usage Guide](#)
- TN1180, [LatticeECP3 High-Speed I/O Interface](#)
- TN1181, [Power Consumption and Management for LatticeECP3 Devices](#)
- TN1182, [LatticeECP3 sysDSP Usage Guide](#)
- TN1184, [LatticeECP3 Soft Error Detection \(SED\) Usage Guide](#)
- TN1189, [LatticeECP3 Hardware Checklist](#)
- TN1215, [LatticeECP2MS and LatticeECP2S Devices](#)
- TN1216, [LatticeECP2/M and LatticeECP3 Dual Boot Feature Advanced Security Encryption Key Programming Guide for LatticeECP3](#)
- TN1222, [LatticeECP3 Slave SPI Port User's Guide](#)

For further information on interface standards refer to the following websites:

- JEDEC Standards (LVTTTL, LVCMOS, SSTL, HSTL): www.jedec.org
- PCI: www.pcisig.com

Date	Version	Section	Change Summary
September 2009	01.4	Architecture	Corrected link in sysMEM Memory Block section.
			Updated information for On-Chip Programmable Termination and modified corresponding figure.
			Added footnote 2 to On-Chip Programmable Termination Options for Input Modes table.
			Corrected Per Quadrant Primary Clock Selection figure.
		DC and Switching Characteristics	Modified -8 Timing data for 1024x18 True-Dual Port RAM (Read-Before-Write, EBR Output Registers)
			Added ESD Performance table.
			LatticeECP3 External Switching Characteristics table - updated data for $t_{DIBGDDR}$, t_{W_PRI} , t_{W_EDGE} and $t_{SKEW_EDGE_DQS}$.
			LatticeECP3 Internal Switching Characteristics table - updated data for t_{COO_PIO} and added footnote #4.
			sysCLOCK PLL Timing table - updated data for f_{OUT} .
			External Reference Clock Specification (refclkp/refclkn) table - updated data for $V_{REF-IN-SE}$ and $V_{REF-IN-DIFF}$.
			LatticeECP3 sysCONFIG Port Timing Specifications table - updated data for t_{MWC} .
			Added TRLVDS DC Specification table and diagram.
			Updated Mini LVDS table.
August 2009	01.3	DC and Switching Characteristics	Corrected truncated numbers for V_{CCIB} and V_{CCOB} in Recommended Operating Conditions table.
July 2009	01.2	Multiple	Changed references of “multi-boot” to “dual-boot” throughout the data sheet.
		Architecture	Updated On-Chip Programmable Termination bullets.
			Updated On-Chip Termination Options for Input Modes table.
			Updated On-Chip Termination figure.
		DC and Switching Characteristics	Changed min/max data for $FREF_PPM$ and added footnote 4 in SERDES External Reference Clock Specification table.
			Updated SERDES minimum frequency.
		Pinout Information	Corrected MCLK to be I/O and CCLK to be I in Signal Descriptions table
May 2009	01.1	All	Removed references to Parallel burst mode Flash.
		Introduction	Features - Changed 250 Mbps to 230 Mbps in Embedded SERDES bullet section and added a footnote to indicate 230 Mbps applies to 8b10b and 10b12b applications.
			Updated data for ECP3-17 in LatticeECP3 Family Selection Guide table.
			Changed embedded memory from 552 to 700 Kbits in LatticeECP3 Family Selection Guide table.
		Architecture	Updated description for CLKFB in General Purpose PLL Diagram.
			Corrected Primary Clock Sources text section.
			Corrected Secondary Clock/Control Sources text section.
			Corrected Secondary Clock Regions table.
			Corrected note below Detailed sysDSP Slice Diagram.
			Corrected Clock, Clock Enable, and Reset Resources text section.
			Corrected ECP3-17 EBR number in Embedded SRAM in the LatticeECP3 Family table.
			Added On-Chip Termination Options for Input Modes table.
			Updated Available SERDES Quads per LatticeECP3 Devices table.